

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Yuichi KUNORI

Serial No.: 09/469,497

Filed: December 22, 1999

Group Art Unit: 2187

Examiner: J. Song

For: MULTILEVEL STORAGE NONVOLATILE SEMICONDUCTOR MEMORY DEVICE ENABLING
HIGH-SPEED DATA READING AND HIGH-SPEED DATA WRITING

THE COMMISSIONER FOR PATENTS AND TRADEMARKS
Washington, DC 20231

Dear Sir:

Transmitted herewith is an Amendment in the above identified application.

☐
☐
☐

No additional fee is required.

Applicant is entitled to small entity status under 37 CFR 1.27

Also attached:

The fee has been calculated as shown below:

| | NO. OF CLAIMS | HIGHEST PREVIOUSLY PAID FOR | EXTRA CLAIMS | RATE | FEE |
|---------------------------------|------------------|-----------------------------------|-----------------|-----------|---------|
| Total Claims | 17 | 20 | 0 | \$18.00 = | \$0.00 |
| Independent Claims | 4 | 3 | 1 | \$84.00 = | \$84.00 |
| Multiple claims newly presented | | | | | \$0.00 |
| Fee for extension of time | | | | | \$0.00 |
| Total of Above Calculations | | | | | \$84.00 |

☒ Please charge my Deposit Account No. 500417 in the amount of \$84.00. An additional copy of this transmittal sheet is submitted herewith.

☒ The Commissioner is hereby authorized to charge payment of any fees associated with this communication or credit any overpayment, to Deposit Account No. 500417, including any filing fees under 37 CFR 1.16 for presentation of extra claims and any patent application processing fees under 37 CFR 1.17.

Respectfully submitted,

MCDERMOTT, WILL & EMERY



Gene Z. Robinson

Registration No. 33,351

03/05/2002 JBALINAN 00000052 500417 09469497

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84.00 CH

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Technology Center 2100

Docket No.: 49657-586



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PATENT

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DEVICE ENABLING HIGH-SPEED DATA READING AND HIGH-SPEED
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PRELIMINARY AMENDMENT

Commissioner for Patents
Washington, DC 20231

Sir:

Please amend the above-identified application, prior to examination thereof, as
follows:

IN THE CLAIMS

Please add the following new claims to the application:

91 Sub 4
-- 13. A method for reading a plurality of data from a non-volatile
semiconductor memory device, said non-volatile semiconductor memory device
including a memory cell storing said plurality of data and a data output node for
outputting said data, said method comprising the steps of:

reading a part of said plurality of data from said memory cell;

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